Gate Leakage Suppression and Breakdown Voltage Enhancement in p-GaN HEMTs using Metal/Graphene Gates

Guangnan Zhou, Zeyu Wan, Gaiying Yang, Yang Jiang, Robert Sokolovskij, Hongyu Yu, and Guangrui (Maggie) Xia

Abstract—in this work, single-layer intrinsic and fluorinated graphene were investigated as gate insertion layers for normally-off p-GaN gate HEMTs, which were sandwiched between the Ti/p-GaN and Ti/SiN. Compared to the metal/p-GaN HEMTs without graphene, the insertion of graphene can increase the $I_{ON}/I_{OFF}$ ratios by a factor of 50, increase the $V_{TH}$ by 0.30 V and reduce the off-state gate leakage by 50 times. Additionally, this novel gate structure has better thermal stability. After thermal annealing at 350 °C, gate breakdown voltage holds at 12.1 V, which is first reported for Schottky gate p-GaN HEMTs. This is considered to be a result of the 0.24 eV increase in Schottky barrier height and the better quality of the graphene/p-GaN and graphene/SiN interfaces. This approach is very effective in improving the $I_{ON}/I_{OFF}$ ratio and gate BV of normally-off GaN HEMTs.

Index Terms—p-GaN high electron mobility transistor (HEMT), graphene, gate leakage, gate breakdown

I. INTRODUCTION

Gallium nitride (GaN) possesses excellent physical properties, such as a high critical electric field and a high saturation velocity [1-3], which is ideal for devices with a low specific ON-resistance ($R_{ON}$), a high breakdown voltage and a high operation switching frequency. For switch applications, normally-off transistors are required to provide adequate safety conditions [4-5]. Among many options of normally-off HEMTs [6-8], recessed gate metal-insulator-semiconductor-HEMTs (MIS-HEMTs) and p-GaN gate HEMTs (which lift up the conduction band) have been considered as the two most promising approaches [9-10].

Reducing the gate leakage current remains a big challenge for p-GaN gate HEMTs [11-13]. The forward gate leakage current limits the gate voltage swing and causes drive losses, while the reverse one can lead to the off-state power consumption [14]. Previous studies in MIS-HEMTs revealed that fluorinated graphene can serve as a barrier layer between Al$_2$O$_3$ and GaN, which contributed to a suppression of gate leakage current by two orders of magnitude [15]. Graphene can act as a strong barrier to atom diffusion and saturate the dangling bonds and defects on the surface [16, 17]. However, there have not been any reports on the effectiveness of graphene in p-GaN HEMTs, which was addressed in this work.

II. DEVICE STRUCTURE AND FABRICATION

The p-GaN gate HEMTs were fabricated on 100 nm p-GaN/15 nm Al$_2$Ga$_{0.8}$In$_{0.7}$N/0.7 nm AlN/4.5 μm GaN epi-structures grown on Si (111) substrates by metal organic chemical vapor deposition (MOCVD) provided by Enkris Semiconductor Inc. Fig. 1 shows the schematic cross-section of the devices. Prior to the deposition of gate metals (40 nm Ti/100 nm Au), single layer graphene grown by chemical vapor deposition (CVD) on Cu foils was transferred to part of the sample surface via the “polymethyl methacrylate (PMMA)-mediated” wet-transfer approach [18].

![Fig. 1. (a) Schematic of the device structure; (b) Cross-section of the device characterized by a scanning transmission electron microscope (STEM) showing the edge of a p-GaN gate and the p-GaN/AlGaN/GaN structure.](image)

Two types of graphene, intrinsic (I-graphene) and fluorinated graphene (F-graphene), were investigated. F-graphene was realized by exposing the I-graphene to SF$_6$.
plasma. In this experiment, the quality and the cleanliness of the transferred graphene are crucial, as the metal/semiconductor barrier height heavily depends on the surface states and defects. Especially, the PMMA residuals could lead to Fermi-level pinning at the metal/graphene/p-GaN junction, which would eventually result in the malfunction of these devices [19]. As illustrated in Fig. 2, the Raman spectra and SEM pictures show that the transferred graphene has a high quality ($I_{2D}/I_G \approx 2$) with negligible PMMA contaminations [20].

Fig. 2. The transferred graphene characterized by (a) Raman spectroscopy and (b) SEM, a few PMMA residuals are shown intentionally as noted by the arrows.

III. RESULTS AND DISCUSSION

A. HEMTs results

The HEMTs with and without graphene are from the same wafer piece. The gate leakage, transfer and output characteristics of the HEMTs are shown in Fig. 3.

![Gate leakage characteristics](image1)

![Transfer characteristics](image2)

![Output characteristics](image3)

Fig. 3. Comparison of the device performance of the p-GaN HEMTs with I-graphene, F-graphene and without graphene: (a) gate leakage characteristics under $V_{GS} = 0$ V; (b) output characteristics ($V_G$ from $V_{TH} - 1.5 V$ to $V_{TH} + 5 V$); (c) transfer characteristics under $V_{DS} = 1$ V, the inset figure is transfer characteristics plotted in linear scale; and (d) $V_{TH}$ uniformity characterization.

Compared to the HEMTs with Ti/p-GaN gate structures, those with Ti/I-graphene/p-GaN and Ti/F-graphene/p-GaN gate structures have about one order of magnitude lower gate leakage at forward bias and 2 orders of magnitude at a reverse bias. Additionally, the HEMTs with graphene have higher threshold voltage ($V_{TH}$) defined at $I_{DS} = 10 \mu A/mm$ (0.32 V for I-graphene and 0.28 V for F-graphene). More importantly, the insertion of graphene increased the $I_{ON}/I_{OFF}$ ratio at least one order of magnitude for both types of graphene. Detailed comparison of the extracted DC parameters between three types of devices is shown in Table I. The statistical data of $V_{TH}$ is shown in Fig. 3 (d). The average $V_{TH}$ values of the devices without graphene, with I-graphene and with F-graphene are 1.58 V, 1.86 V and 1.84 V, respectively. The increase of $V_{TH}$ should be attributed to higher Schottky barrier height ($\Phi_B$) and p-type doping in graphene introduced in the “PMMA-mediated” wet-transfer process [18]. In summary, the insertion of graphene reduced the gate leakage current and increased $V_{TH}$ without sacrificing any output performances.

### TABLE I

<table>
<thead>
<tr>
<th>Parameters</th>
<th>No graphene</th>
<th>I-Graphene</th>
<th>F-Graphene</th>
</tr>
</thead>
<tbody>
<tr>
<td>$I_D$ ($V_G = 8V$) (mA/mm)</td>
<td>~ 2</td>
<td>~ 0.1</td>
<td>~ 0.1</td>
</tr>
<tr>
<td>$I_{DS}$ (mA/mm)</td>
<td>$2.5 \times 10^{-6}$</td>
<td>$3.6 \times 10^{-6}$</td>
<td>$1.2 \times 10^{-6}$</td>
</tr>
<tr>
<td>$V_{TH}$ (V)</td>
<td>1.54</td>
<td>1.86</td>
<td>1.82</td>
</tr>
<tr>
<td>$R_{ON}$ (Ω•mm)</td>
<td>12.4</td>
<td>12.8</td>
<td>11.9</td>
</tr>
<tr>
<td>Gate BV (V)</td>
<td>9.8</td>
<td>12.1</td>
<td>12.0</td>
</tr>
</tbody>
</table>

B. Effects of Graphene during Annealing Treatment

In practice, passivation layers are necessary for metal pads and interconnect protection. This means that the gate metal/p-GaN interfaces will commonly experience some low-temperature thermal budgets. For the gate-metal-first process, the interface will undergo an even higher thermal budget for S/D contact annealing [13]. To investigate the effects of graphene during these thermal steps, the devices were annealed at 350 °C in N$_2$ for 5 min. Fig. 4 presents the gate leakage characteristics and gate breakdown voltage (BV) before and after annealing. As illustrated in Fig. 4, in the case of forward $V_G$ bias, all the devices have a considerable increase in gate leakage. This should be due to the reduction of $\Phi_B$. After the annealing, the gate BV of the devices without graphene was 9.80 V whereas the devices with graphene broke down at 12.05 V. To our knowledge, this is the highest gate BV that has been reported in HEMTs with p-GaN Schottky gates. This improvement in gate BV is crucial for p-GaN gate HEMT device for power switching applications.

![Gate leakage and breakdown voltage before and after annealing](image4)
C. Mechanism study with Ti/graphene/p-GaN Schottky diodes

To get further insights into the role of graphene on metal/p-GaN interfaces, STEM images were obtained. However, no significant interface quality or morphology differences have been found between the two interfaces (Fig. 5).

![Cross-section STEM of (a) Au/Ti/P-GaN after 350 °C 5 min annealing and (b) Au/Ti/Graphene/P-GaN after 350 °C min annealing.](image)

Besides the material analysis, Au/Ti/graphene/p-GaN Schottky contacts have been fabricated as seen in the inset of Fig. 6(a). Considering the fact that the I-graphene and F-graphene had a little distinction in the previous experiments, only I-graphene was studied here. This test structure consists of two Schottky contacts back-to-back [21]. The I–V measurements were carried out in the bias range of 0 to 6 V. Before annealing, the systems with and without I-graphene have comparable current density. Combined with the thermionic field emission model in literature [13] [22], the $\Phi_B$ were extracted from the data (Fig. 6(b)), which is 2.08 eV for the contacts without graphene and 2.09 eV for those with I-graphene, respectively. After annealing the sample at 350 °C in N$_2$ for 5 min, $\Phi_B$ decreased to 1.65 eV and 1.89 eV, which results in approximately one order of magnitude smaller current in the sample with graphene. These data are consistent with the experimental value reported in the literature for Ti/p-GaN interfaces [13].

![I-V characteristics acquired in back-to-back diodes. Inset: Schematics of the sample structure; (b) Temperature dependence of the current measured at V = 40.2 V in back-to-back Schottky contacts. The symbols are measured data. The lines are the fitting curves.](image)

Based on this evidence, it can be deduced that graphene can help maintain a more stable metal/p-GaN interface during annealing. In $V_G$ > 0 regime, the larger $\Phi_B$ contributes to a lower gate leakage current and the higher $V_{TH}$. Graphene can also prevent the decrease of gate BV during annealing. In the $V_G$ < 0 regime, as the p-GaN/AlGaN/GaN junction and p-GaN sidewall path are the dominant factor for gate leakage [12], it is likely that the better metal/graphene/SiN$_x$ interface reduces the leakage via the SiN$_x$ edges.

IV. Conclusion

In this work, intrinsic and fluorinated graphene were investigated as gate insertion layers for normally-OFF p-GaN HEMTs, which formed metal/graphene/p-GaN interfaces in the middle and metal/graphene/ SiN$_x$ on the two sides. 50 times larger $I_{ON}/I_{OFF}$ ratios, 0.30 V higher $V_{TH}$ increase, 50 times off-state gate leakage reduction have been achieved by the insertion of graphene. For the first time, 12.1 V gate BV has been achieved with I-graphene for Schottky gate p-GaN HEMTs. This is considered to be the result of a 0.24 eV higher $\Phi_B$, and the better graphene/p-GaN and graphene/SiN$_x$ interfaces. As single-layer graphene can be prepared in wafer-size areas [23], This approach is mass-production compatible and very effective in improving the $I_{ON}/I_{OFF}$ ratios and increasing $V_{TH}$ and gate BV of p-GaN gate HEMTs.

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References


